

Sergei Chebotarev

List of Publications by Year in descending order

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papers

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docs citations

26
times ranked

18
citing authors

#	ARTICLE	IF	CITATIONS
1	Ion beam crystallization of InAs/GaAs(001) nanostructures. Technical Physics Letters, 2015, 41, 661-664.	0.7	17
2	Ion beam deposition of photoactive nanolayers for silicon solar cells. Inorganic Materials, 2012, 48, 439-444.	0.8	14
3	Synthesis and properties of $\text{In}_x\text{Al}_y\text{Ga}_{1-x-y}\text{PzAs}_z/\text{GaAs}$ heterostructures. Inorganic Materials, 2017, 53, 1217-1227.	0.8	14
4	Formation and use of positioning marks in scanning probe microscopy. Technical Physics Letters, 2010, 36, 737-738.	0.7	13
5	Photoluminescence of $i\text{-Ga} \times \text{In}_1 \hat{=} \times \text{As}/n\text{-GaAs}$ heterostructures containing a random InAs quantum dot array. Inorganic Materials, 2011, 47, 816-818.	0.8	13
6	A study of photosensitive InAs/GaAs heterostructures with quantum dots grown by ion-beam deposition. Journal of Surface Investigation, 2011, 5, 559-562.	0.5	12
7	Correlation between the size and photoluminescence spectrum of quantum dots in InAs-QD/GaAs. Journal of Surface Investigation, 2013, 7, 36-40.	0.5	12
8	Features in the formation of Ge/Si multilayer nanostructures under ion-beam-assisted crystallization. Technical Physics Letters, 2013, 39, 726-729.	0.7	12
9	Structure of Ge nanoclusters grown on Si(001) by ion beam crystallization. Inorganic Materials, 2013, 49, 435-438.	0.8	11
10	Regularities of ion-beam-induced crystallization and properties of InAs-QD/GaAs(001) semiconductor nanoheterostructures. Nanotechnologies in Russia, 2016, 11, 435-443.	0.7	11
11	Obtaining and doping of InAs-QD/GaAs(001) nanostructures by ion beam sputtering. Beilstein Journal of Nanotechnology, 2017, 8, 12-20.	2.8	10
12	Morphology and Optical Investigations of InAs-QD/GaAs Heterostructures Obtained by Ion-Beam Sputtering. Journal of Nanotechnology, 2016, 2016, 1-9.	3.4	7
13	Carrier transport in multilayer InAs/GaAs quantum dot heterostructures grown by ion beam crystallization. Inorganic Materials, 2015, 51, 197-200.	0.8	5
14	Growth and properties of GaInPSbAs isoperiodic solid solutions on indium arsenide substrates. Physics of the Solid State, 2016, 58, 1751-1757.	0.6	5
15	Effect of bismuth on parameters of a GaInSbAsP solid solution grown on GaSb substrates. Inorganic Materials, 2017, 53, 57-64.	0.8	5
16	Germanium layers grown by zone thermal crystallization from a discrete liquid source. Journal of Physics: Conference Series, 2017, 917, 032008.	0.4	5
17	Specific features of doping with antimony during the ion-beam crystallization of silicon. Semiconductors, 2016, 50, 545-548.	0.5	4
18	Variation of the photoluminescence spectrum of InAs/GaAs heterostructures grown by ion-beam deposition. Beilstein Journal of Nanotechnology, 2018, 9, 2794-2801.	2.8	4

#	ARTICLE	IF	CITATIONS
19	Study of the Structural and Luminescence Properties of InAs/GaAs Heterostructures with Bi-Doped Potential Barriers. <i>Semiconductors</i> , 2018, 52, 729-733.	0.5	3
20	Thin-layer GaInSbAsPBi/GaSb heterostructures obtained from liquid phase in a temperature-gradient field. <i>Crystallography Reports</i> , 2017, 62, 139-143.	0.6	2
21	Simulation of electrical conductivity of silicon diodes with bismuth implanted-ion profiles. <i>Journal of Physics: Conference Series</i> , 2018, 1124, 071009.	0.4	1
22	Investigation of the Structural Perfection of Thin-Film InAlGaPAs/GaAs Heterostructures. <i>Journal of Surface Investigation</i> , 2018, 12, 466-472.	0.5	1
23	Features of a zone thermal crystallization semiconductor thin films grown from a discrete liquid source. <i>Journal of Physics: Conference Series</i> , 2018, 1124, 022015.	0.4	0
24	Wireless software-hardware complex for testing semiconductor structures. <i>Journal of Physics: Conference Series</i> , 2019, 1410, 012202.	0.4	0
25	DEVELOPMENT OF TECHNOLOGY FOR PRODUCTION OF SOFT CHEESE PRODUCT BASED ON THREE-COMPONENT RAW MATERIAL MIXTURE. <i>Vestnik VostoĤno-Sibirskogo Gosudarstvennogo Universiteta Tehnologij I UpravleniĤ</i> , 2021, , 5-12.	0.2	0
26	Technology of production of kumis drink enriched with iodine-glycosideĤcomplex. <i>Vestnik VoroneĤskogo Gosudarstvennogo Universiteta inĤeneryh Tehnologij</i> , 2021, 83, 137-142.	0.3	0